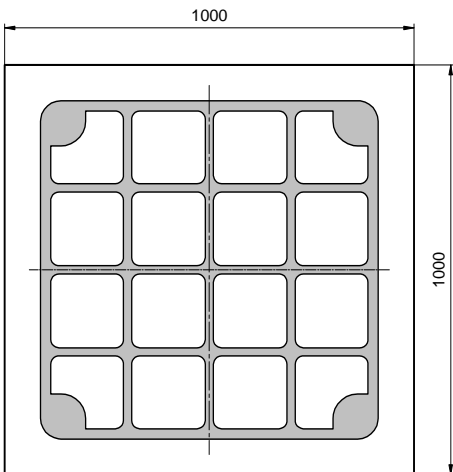


Radiation	Type	Technology	Electrodes
Infrared	DDH	AlGaAs/AlGaAs	N (cathode) up

	typ. dimensions (µm)	
	<u>typ. thickness</u> 150 (±25) µm <u>cathode</u> gold alloy, 1.5 µm <u>anode</u> gold alloy, 0.5 µm structured, 25% covered	

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F = 20 mA	V _F		1.5	1.8	V
Forward voltage ²	I _F = 350 mA	V _F		1.9		V
Reverse voltage	I _R = 10 µA	V _R	5			V
Radiant power ¹	I _F = 20 mA	Φ _e	2.0	2.5		mW
Radiant power ²	I _F = 350 mA	Φ _e		35		mW
Peak wavelength	I _F = 20 mA	λ _P	740	750	760	nm
Spectral bandwidth at 50%	I _F = 20 mA	Δλ _{0.5}		30		nm
Switching time	I _F = 100 mA	t _r , t _f		60		ns

¹Measured on bare chip on TO-18 header

²Measured on bare chip on TO-18 header and heat sink, 10s current flow (information only)

Labeling

Type	Lot N°	Φ _e (typ) [mW]	V _F (typ) [V]	Quantity
ELC-750-21				

Packing: Chips on adhesive film with wire-bond side on top

Note: All measurements carried out with JENOPTIK Polymer Systems equipment